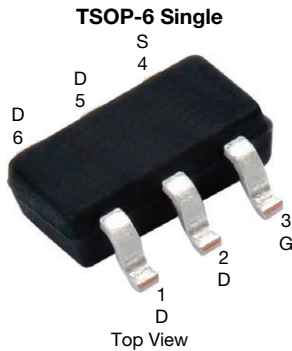


Automotive N-Channel 60 V (D-S) 175 °C MOSFET



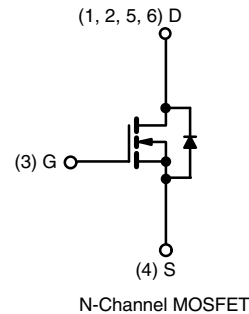
Marking Code: 9Hxxx

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.042
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.063
I_D (A)	7
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3426CEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	60	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	$T_C = 25$ °C	I_D	7	A
	$T_C = 125$ °C		4	
Continuous source current (diode conduction)		I_S	4.6	
Pulsed drain current ^a		I_{DM}	29	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	10	mJ
Single pulse avalanche energy		E_{AS}	5	
Maximum power dissipation	$T_C = 25$ °C	P_D	5	W
	$T_C = 125$ °C		1.6	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction to ambient	PCB mount ^b	R_{thJA}	110	°C/W
Junction to foot (drain)		R_{thJF}	30	

Notes

- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.5	2	2.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$		-	-	± 100	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 300	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	10	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}$	-	0.034	0.042	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.073	
		$V_{GS} = 10\text{ V}$	$I_D = 5\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.092	
		$V_{GS} = 4.5\text{ V}$	$I_D = 4\text{ A}$	-	0.037	0.063	
Forward transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 4\text{ A}$		-	21	-	S
Dynamic ^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 30\text{ V}, f = 1\text{ MHz}$	-	862	1300	pF
Output Capacitance	C_{oss}			-	75	110	
Reverse Transfer Capacitance	C_{rss}			-	29	70	
Total Gate Charge ^c	Q_g	$V_{GS} = 4.5\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 4\text{ A}$	-	6.8	12	nC
Gate-Source Charge ^c	Q_{gs}			-	2.9	-	
Gate-Drain Charge ^c	Q_{gd}			-	2.0	-	
Gate Resistance	R_g	f = 1 MHz		1.55	3.1	5.7	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 7.5\text{ }\Omega$ $I_D \cong 4\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	9	14	ns
Rise Time ^c	t_r			-	3	10	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	19	29	
Fall Time ^c	t_f			-	4	10	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I_{SM}			-	-	29	A
Forward voltage	V_{SD}	$I_F = 1.6\text{ A}, V_{GS} = 0\text{ V}$		-	0.77	1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = 4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		-	19	38	ns
Body diode reverse recovery charge	Q_{rr}			-	18	36	nC
Reverse recovery fall time	t_a			-	15	-	ns
Reverse recovery rise time	t_b			-	4	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-2.1	-	A

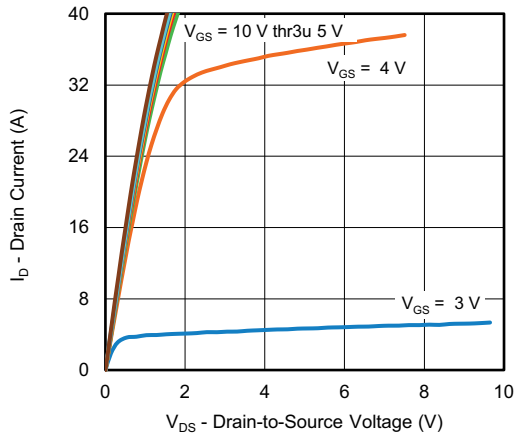
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

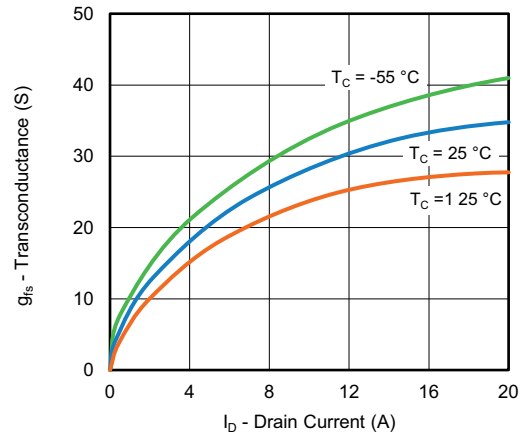
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



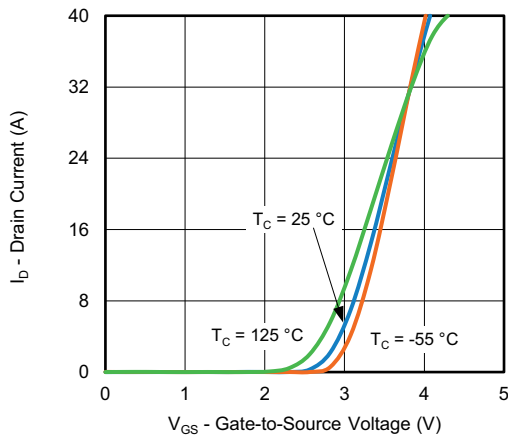
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



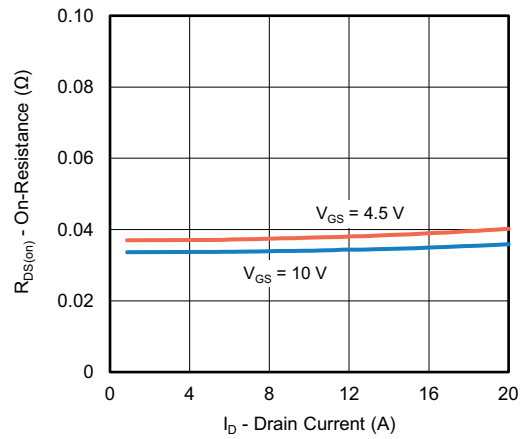
Output Characteristics



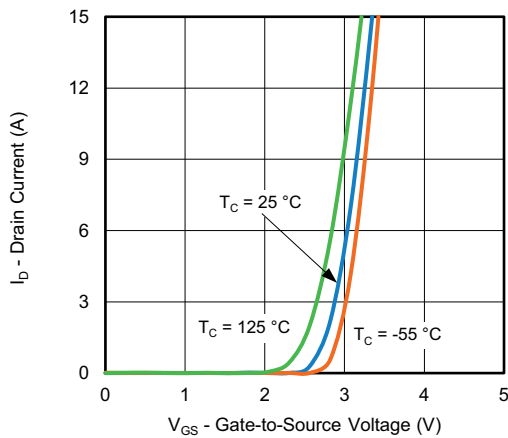
Transconductance



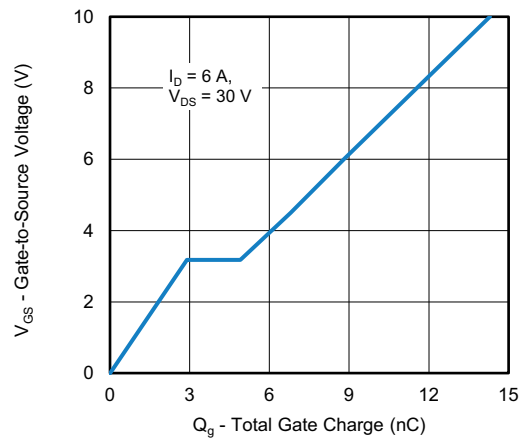
Transfer Characteristics



On-Resistance vs. Drain Current



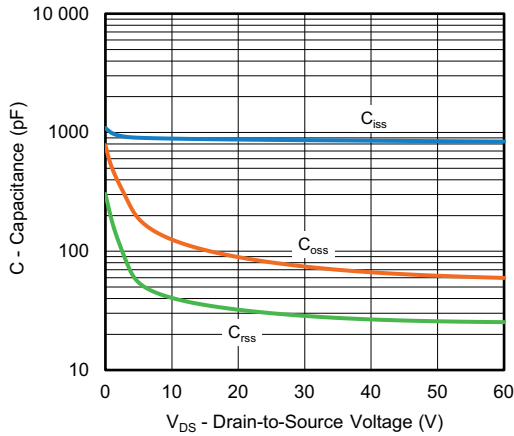
Transfer Characteristics



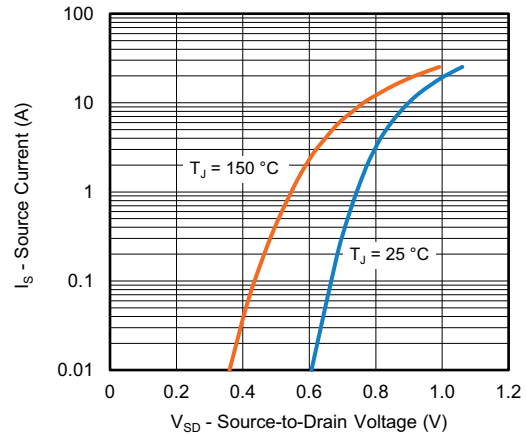
Gate Charge



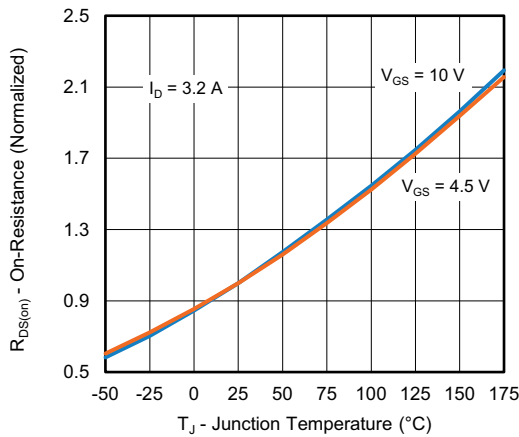
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



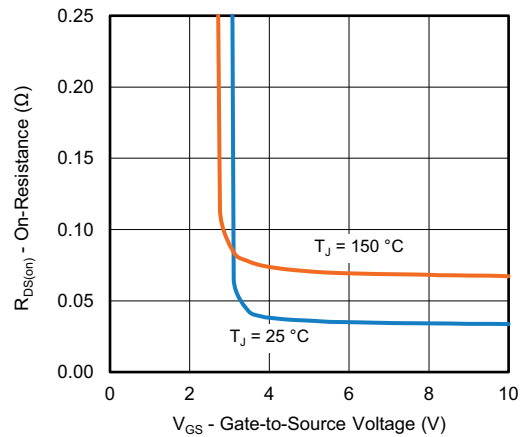
Capacitance



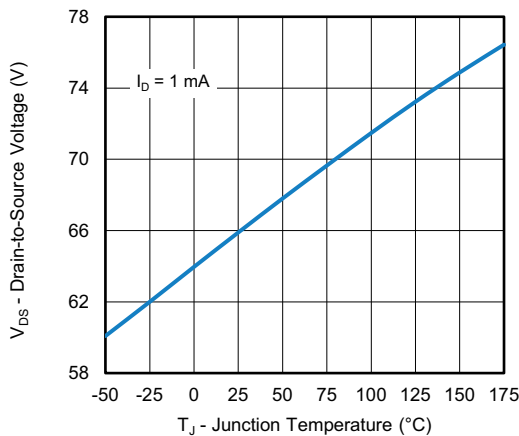
Source Drain Diode Forward Voltage



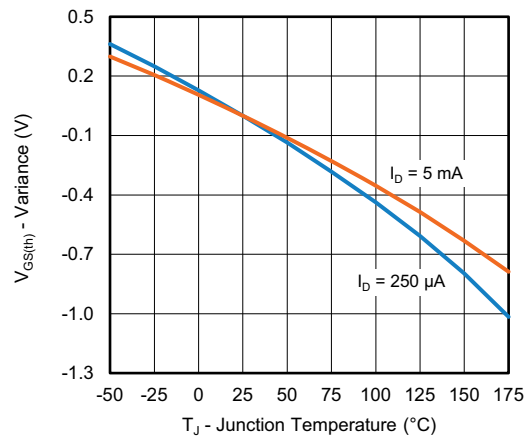
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-Source Voltage



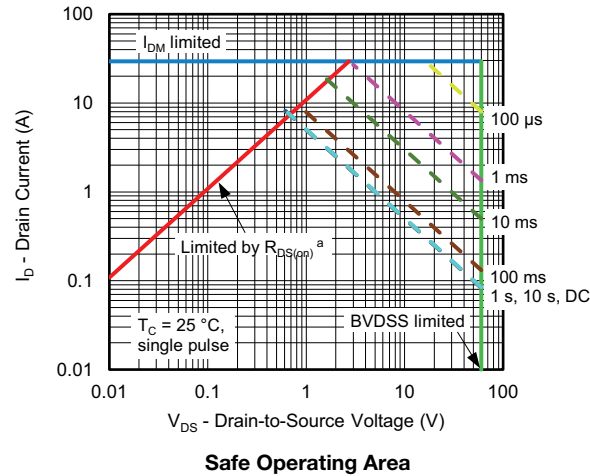
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage

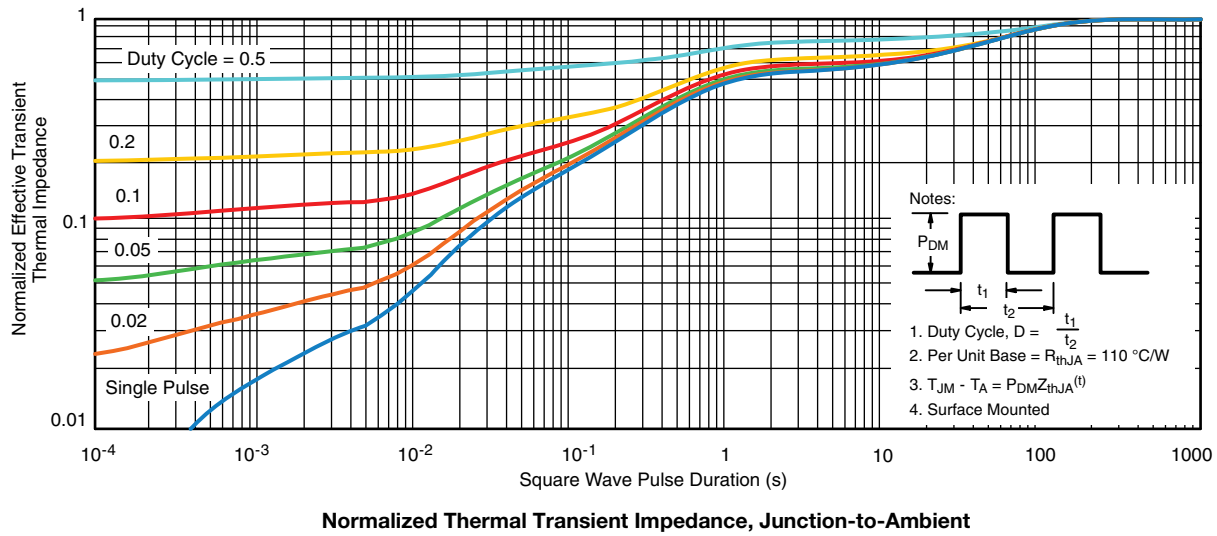


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



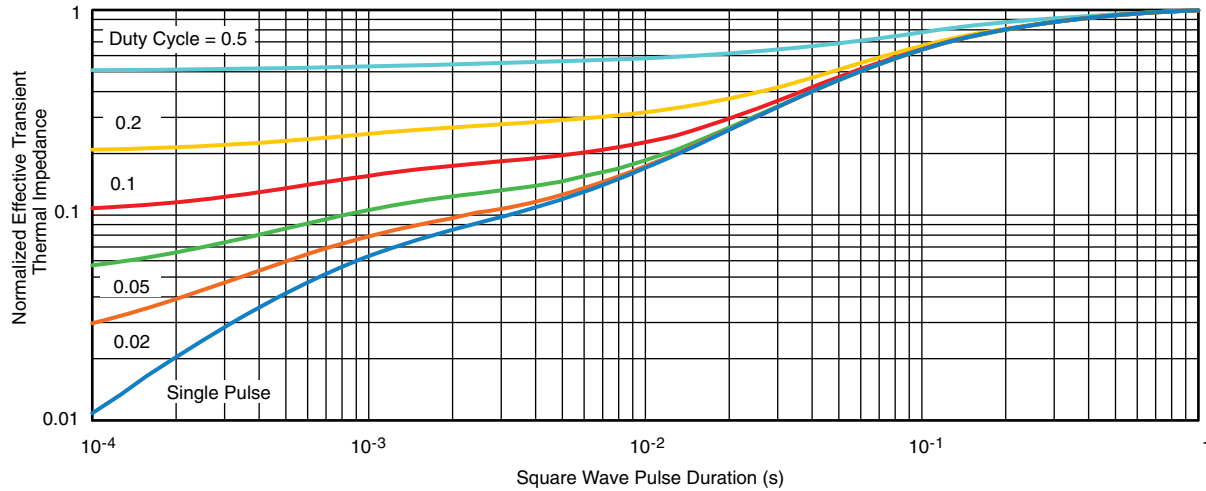
Note

d. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified





THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Foot (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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